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exposure of the ferroelectric film 4 to the plasma atmosphere during a dry etch process. The plasma however has effects upon the ferroelectric 4 that lower its switching charge amount (Qsw). Thus, there has been a fear of causing such problems as worsening the symmetry in hysteresis and deteriorating the characteristics of coerciveness and fatigue.

At page 6, replace the paragraph beginning at line 2 with the following:

2 A method for manufacturing a ferroelectric memory 10 will now be explained concretely with reference to Figure 2 and Figure 3. First, not-shown silicon (Si) substrate is prepared, to form thereon by a CVD technique a first insulation film 12 of silicate glass containing phosphorus (PSG), silicate glass containing boron/phosphorus (BPSG) or the like. Subsequently, as shown in Figure 2(A) the first insulation film 12 is masked by a patterned resist 24 to form a hollow 14 by an RIE (reactive ion etching) technique as anisotropic dry etching. Then, as shown in Figure 2(B), a first conductive film 26 as a gel dry film is formed by a sol-gel technique on a surface of the first insulation film 12 including an inside of the hollow 14. That is, an Ir precursor solution is formed by subjecting a metal alkoxide solution containing irridium (Ir) as an ingredient element to hydrolysis/polycondensation. This solution is applied onto a surface of the first insulation film 12 by a spin coating technique, and then dried into a gel dry film. In an application process using a spin coating technique, the precursor solution dripped on the surface of the first insulation film is splashed away due to a centrifugal force. However, the precursor solution existing inside the hollow 14 will not readily be splashed away. This provides the first conductive film 26 with a film thickness
17 that is greater inside the hollow 14 than the other portion, as shown in Figure 2(B).

At page 7, replace the paragraph beginning at line 23 with the following:

23 According to the present embodiment, a hollow 14 was formed in the top surface of the insulation film 12 so that a lower electrode 16 can be formed inside the hollow 14 by the sol-gel technique including a spin-coating application process. At stated before, it is therefore possible to decrease an etch time to provide a lower electrode 16. This in turn